

Features

- Wide input voltage range: 4.5V – 30V
- High efficiency operation
 - Integrated an 75-mΩ LS-MOSFET and an 110-mΩ HS-MOSFET
 - 91% efficiency at 2A load from 12V to 5V conversion
- Automatic PFM mode at light load (LP6462, LP6462H) and FPWM mode over all load range (LP6462F, LP6462HF)
- $\pm 1\%$ Vref accuracy
- Typical 1.0-MHz switching frequency (LP6462H), 500kHz switching frequency (LP6462)
- COT control scheme with fast load transient response
- Hiccup protection
- Integrated UVLO, OVP, OCP, SCP, and OTP protections
- 600us typical soft-start time
- 1.6mm X 2.9mm SOT23-6 package
- RoHS Compliant and 100% Lead (Pb) Free

Applications

- Industrial PC
- Network/digital video recorder (NVR/DVR)
- TV and TV box
- 12V Industrial bus applications

General Description

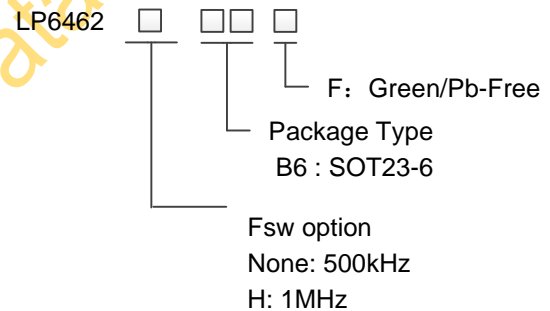
The LP6462 is a synchronous buck converter supporting up to 2A output current. The LP6462 employs an adaptive constant-on-time (COT) control scheme to achieve fast load transient response. The external components are minimized, requiring only one inductor, two resistors, and two capacitors.

The LP6462 supports both aluminum polymer capacitors and ceramic capacitors without extra compensation components.

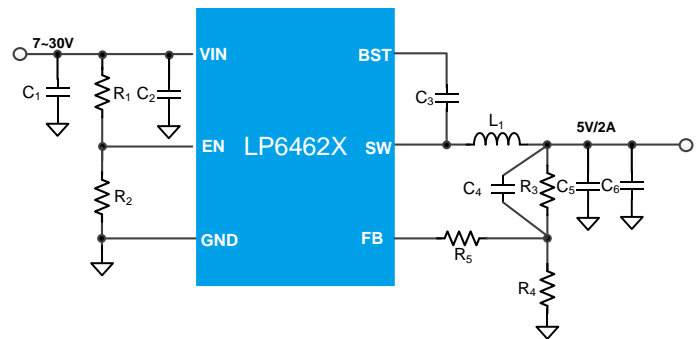
The LP6462 integrates PFM (Pulse Frequency Modulation) operation, which helps maintain the system efficiency at light load. The LP6462 also integrates multiple protection functions, i.e., over-current protection (OCP), over-temperature protection (OTP), under-voltage lockout (UVLO), and short circuit protection (SCP).

The LP6462 is available in a small 6-pin 1.6mmX2.9mm SOT23-6 package.

Order Information



Typical Application Circuit





Device Information

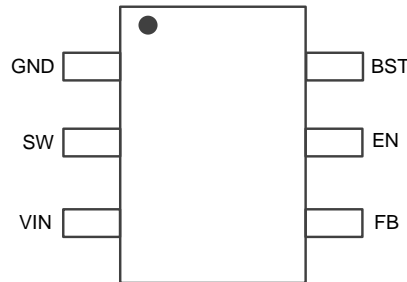
Part Number	Top Marking	Fsw	PFM/FPWM	Shipping
LP6462B6F***	TBD	500kHz	PFM	3K/REEL
LP6462FB6F***	TBD	500kHz	FPWM	3K/REEL
LP6462HB6F	LPS 5JYWX	1MHz	PFM	3K/REEL
LP6462HFB6F	LPS 5cYWX	1MHz	FPWM	3K/REEL

Marking indication: Y: Year code. W: Week code. X: Batch numbers.
 “***”: Product Preview. Contact LowPowerSemi sales for more information.

Preliminary Datasheet



Pin Diagram



SOT23-6
(Top View)

LP6462X Pinout

Pin Description

Pin #	Name	Description
1	GND	Power ground of the IC
2	SW	The switching node of the converter.
3	VIN	IC power supply input.
4	FB	Feedback pin. Use a resistor divider to set the desired output voltage
5	EN	Enable input. This pin can be used to control the system power sequence as well
6	BST	Bootstrap pin. Power supply for high-side MOSFET gate driver. A 0.1- μ F capacitor must be connected between this pin and SW pin.



Absolute Maximum Ratings (Note)

VIN, SW to GND	-----	-0.3V to 32V
EN to GND	-----	-0.3V to 30V
FB to GND	-----	-0.3V to 6.5V
BST to SW	-----	-0.3V to 6.5V
SW to GND (5ns transient)	-----	-5V to 32V
Operating Ambient Temperature Range (TA)	-----	-40°C to 85°C
Maximum Soldering Temperature (at leads, 10 sec)	-----	-260°C

Note: Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD Ratings

HBM (Human Body Model)	-----	2kV
CDM (Charged-device Model)	-----	500V

Thermal Information

θ_{JA} (Junction-to-Ambient Thermal Resistance)	-----	140°C/W
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Recommended Operating Conditions

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT
VIN	Input voltage	4.5		30	V
VOOUT	Output voltage	V _{ref}		7	V
L	Inductor	0.7		13	μH
T _A	Ambient temperature range	-40		85	°C
C _{IN}	Input decoupling capacitor	4.7		100	μF
C _{OUT}	Output capacitor	10		100	μF

Electrical Characteristics

(The specifications are measured under conditions V_{IN} = 12V, T_J = 25°C, unless otherwise specified.)

SYMBOL	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
INPUT SECTION						
V _{ULVO_R}	Input voltage under lockout threshold	V _{IN} rising threshold		4.2	4.5	V
V _{ULVO_H}	UVLO hysteresis	V _{IN} falling threshold		0.2		V
I _{q_VIN}	Input quiescent current	No switching, EN=3V, FB=1.0V		300		μA
BUCK CONVERTER						



SYMBOL	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{LIM}	Low-side valley current limit	T _J =25°C	2.0	3.0	4.0	A
V _{ref}	Reference voltage	T _J =25°C,	0.594	0.6	0.606	V
R _{dson_HS}	High-side FET on resistance	V _{IN} =12V		110		mΩ
R _{dson_LS}	Low-side FET on resistance	V _{IN} =12V		75		mΩ
F _{sw}	Switching frequency	LP6462H		1000		kHz
		LP6462		500		kHz
t _{on-min}	Minimum on-time ^[1]			50		ns
t _{off-min}	Minimum off-time ^[1]	V _{FB} =V _{ref} - 0.2V		100		ns
t _{on-hiccup}	Hiccup on time ^[1]			1		ms
t _{off-hiccup}	Hiccup waiting time ^[1]			10		ms
t _d	EN delay time ^[1]	From EN high to first switching		250		us
t _{ss}	Soft-start time ^[1]	From first switching to 95%V _{ref}		600		us
T _{jsd}	Thermal shutdown threshold	Rising threshold		160		°C
	Thermal shutdown threshold	Falling threshold		135		°C
I _{leak_FB}	FB pin leakage current			0.01		μA
EN Logic						
V _H	EN pin logic high threshold	EN Rising threshold	1.14	1.2	1.26	V
V _{hys}	EN pin threshold hysteresis			0.1		V
	EN pin internal pull-down resistance			1000		kΩ
Output OVP						
V _{OVP_rise}	OVP threshold	V _{OUT} rising edge, reference to V _{ref}	108	110	112	%



SYMBOL	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VovP_fall	OVP hysteresis	VOUT falling edge, reference to Vref		105		%

[1]: Not production tested. Guaranteed by design

Preliminary Datasheet



Typical Characteristics

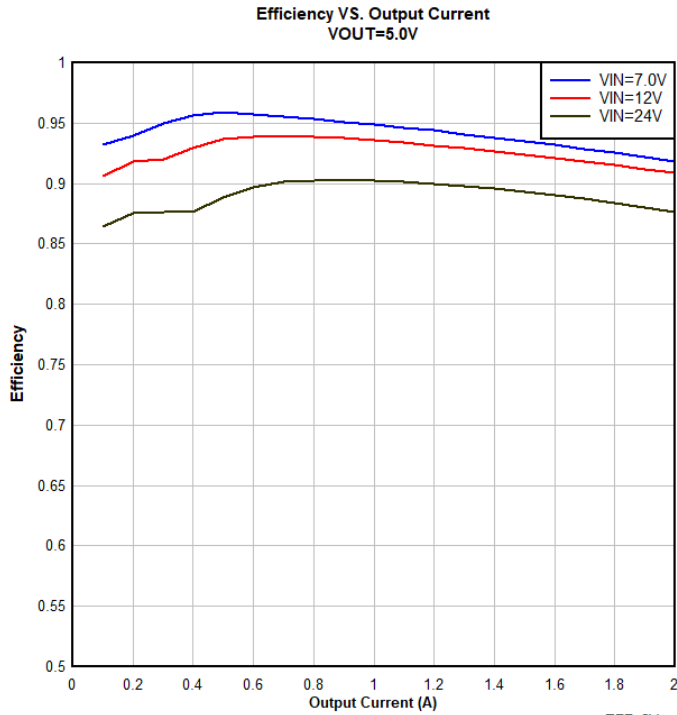


Figure 1. V_{OUT}=5V, Efficiency, L=4.7uH

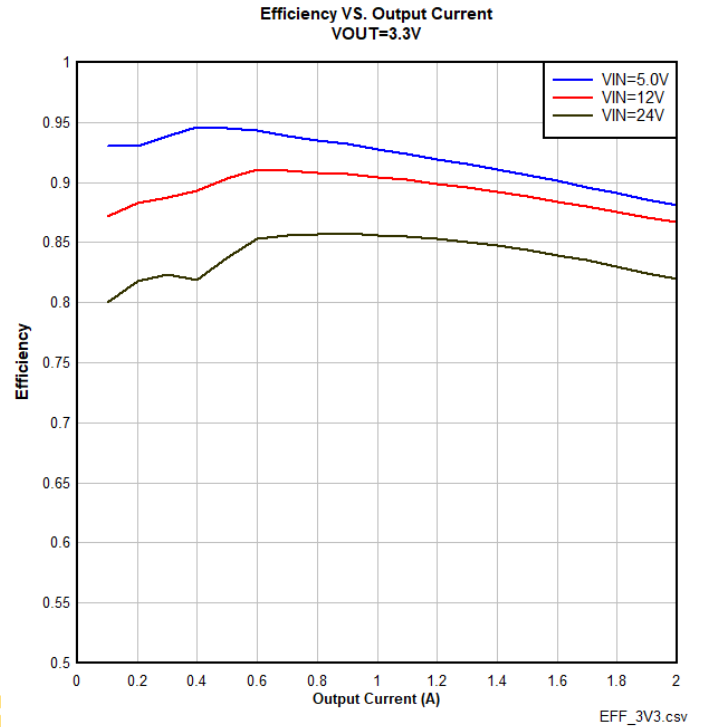


Figure 2. V_{OUT}=3.3V, Efficiency, L=3.3uH

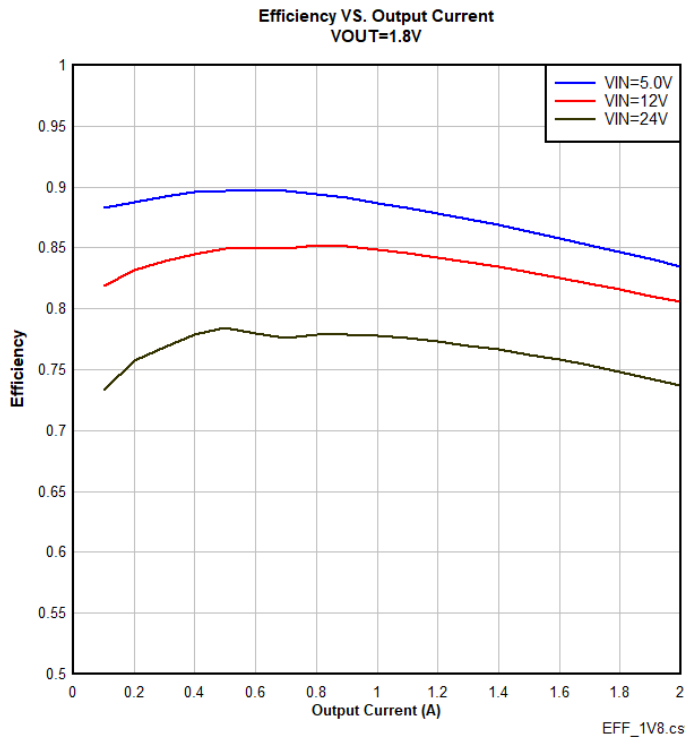


Figure 3. V_{OUT}=1.8V, Efficiency, L=1uH

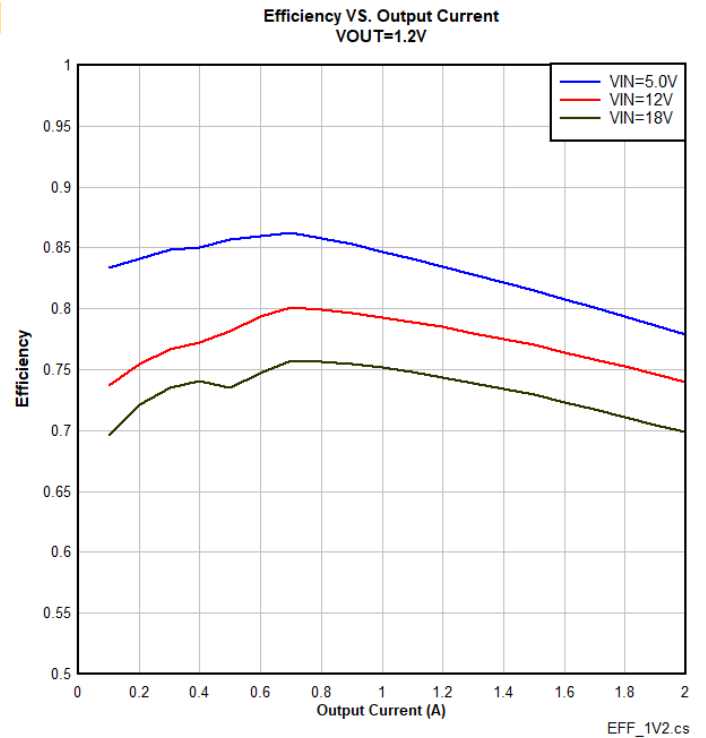


Figure 4. V_{OUT}=1.2V, Efficiency, L=1uH

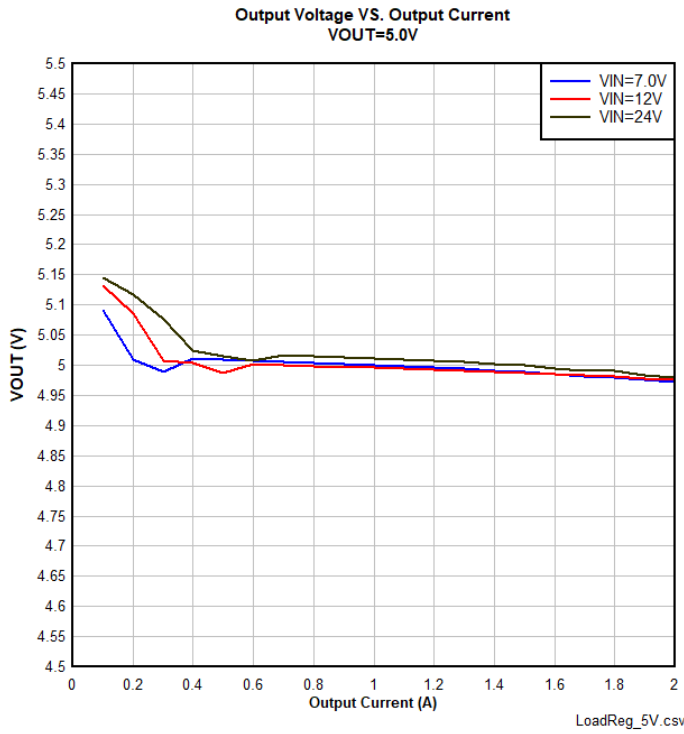


Figure 5. VOUT=5V, Regulation, L=4.7uH

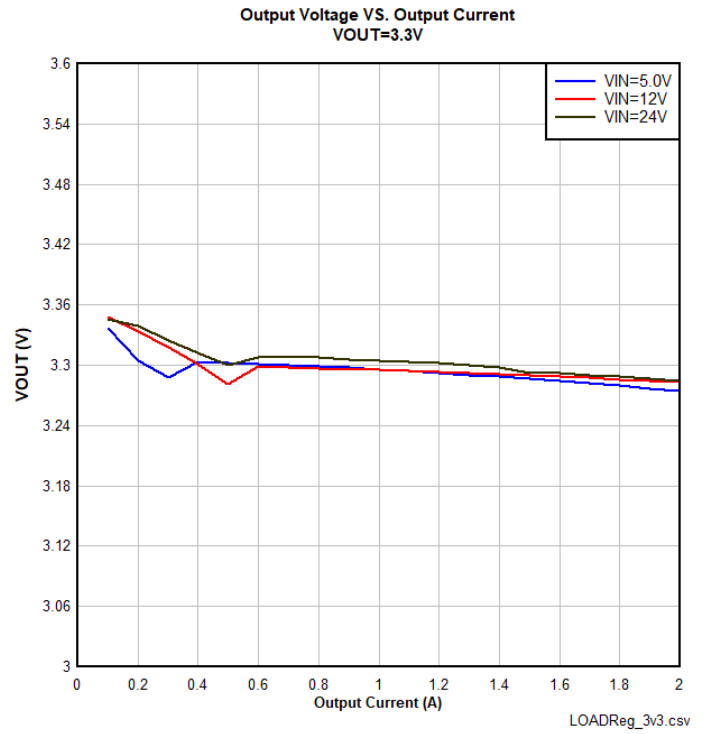


Figure 6. VOUT=3.3V, Regulation, L=3.3uH

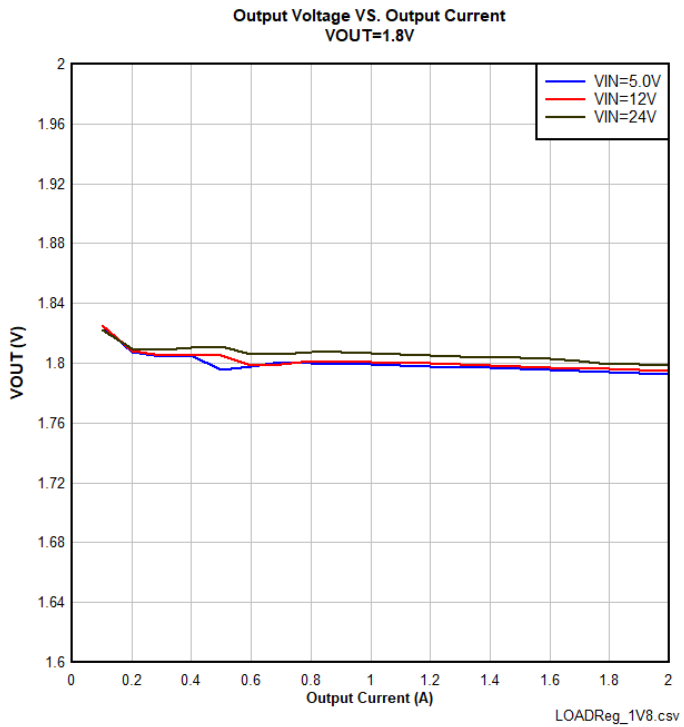


Figure 7. VOUT=1.8V, Regulation, L=1uH

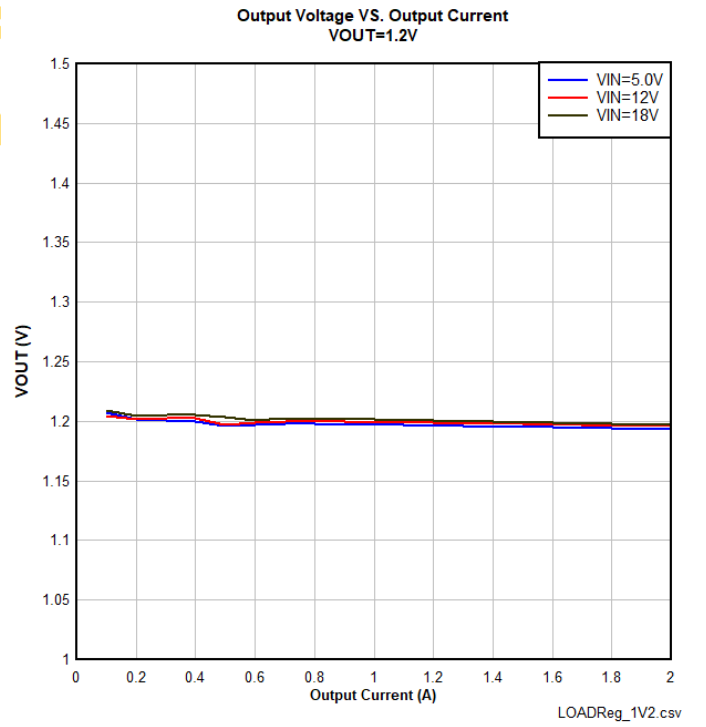


Figure 8. VOUT=1.2V, Regulation, L=1uH

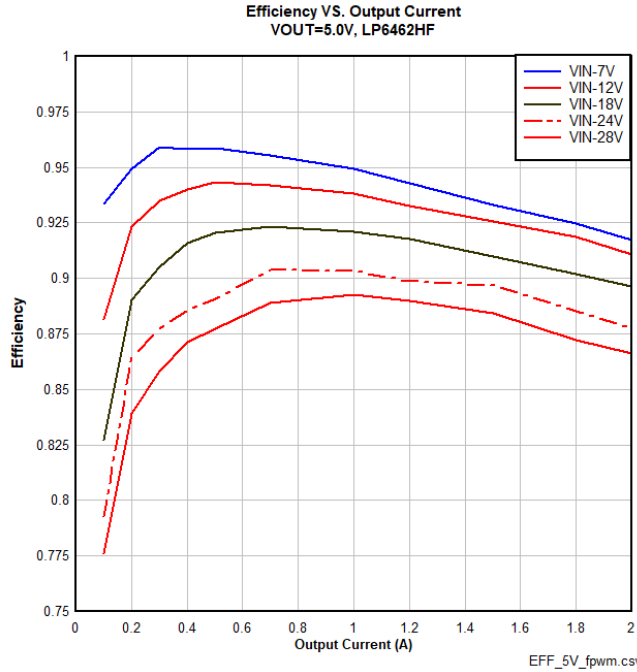


Figure 9. V_{OUT}=5.0V, Efficiency, L=4.7uH

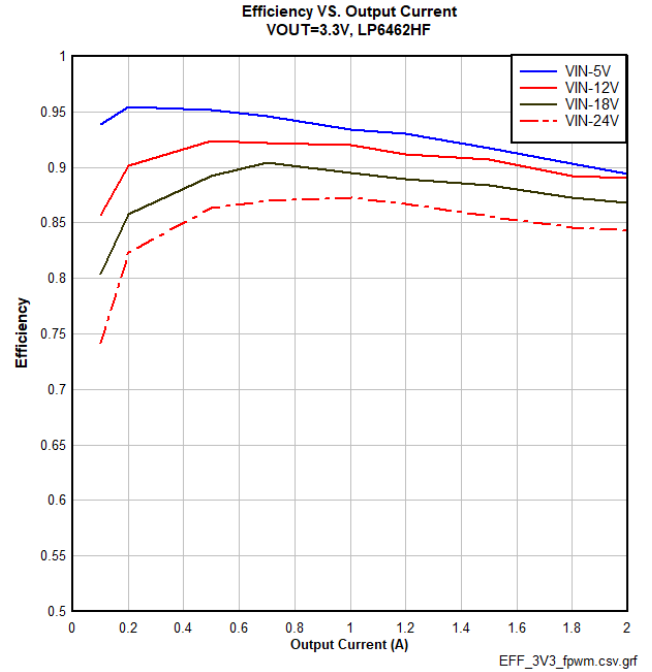


Figure 10. V_{OUT}=3.3V, Efficiency, L=3.3uH

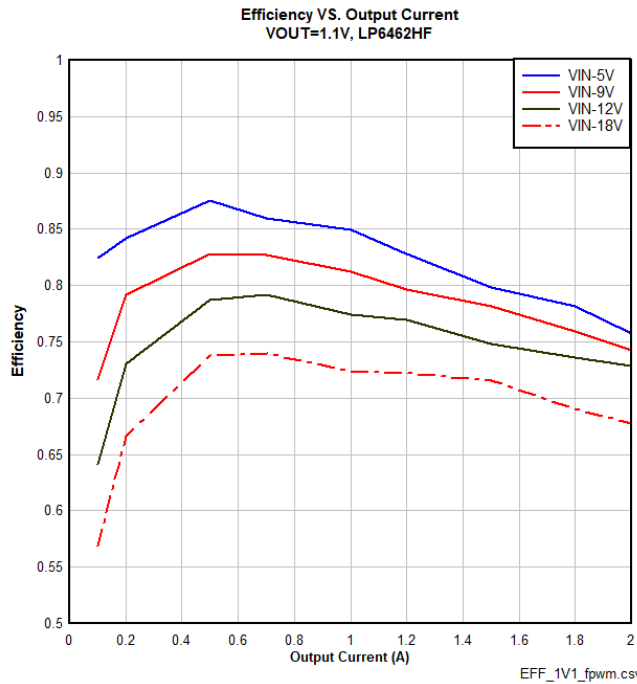


Figure 11. V_{OUT}=1.1V, Efficiency, L=1uH

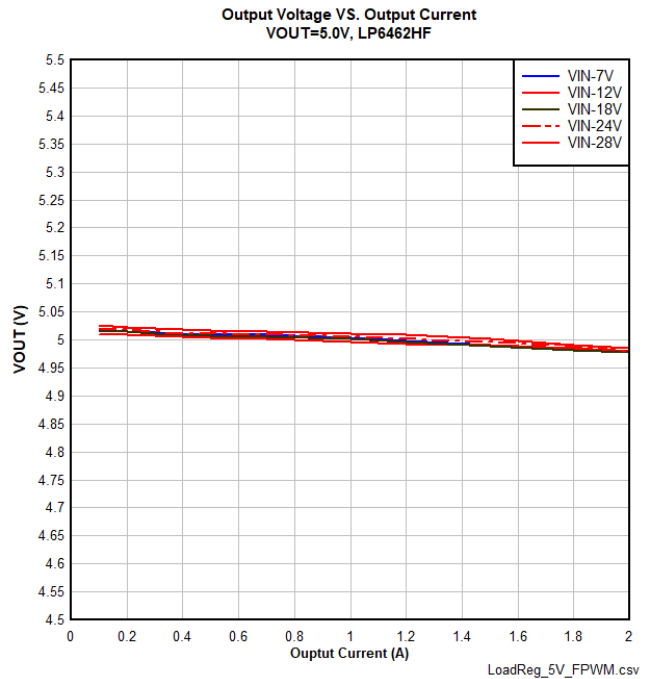


Figure 12. V_{OUT}=5V, Regulation, L=4.7uH

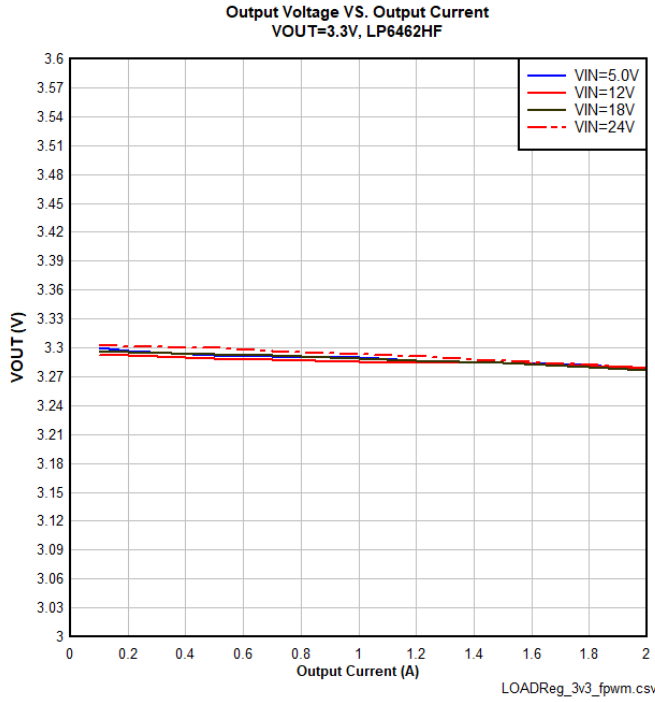


Figure 13. V_{OUT}=3.3V, Efficiency, L=3.3uH

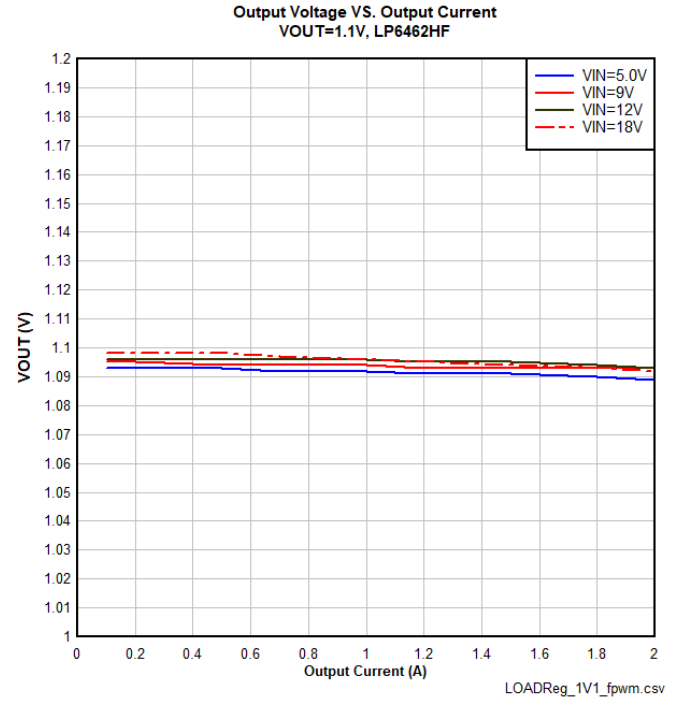
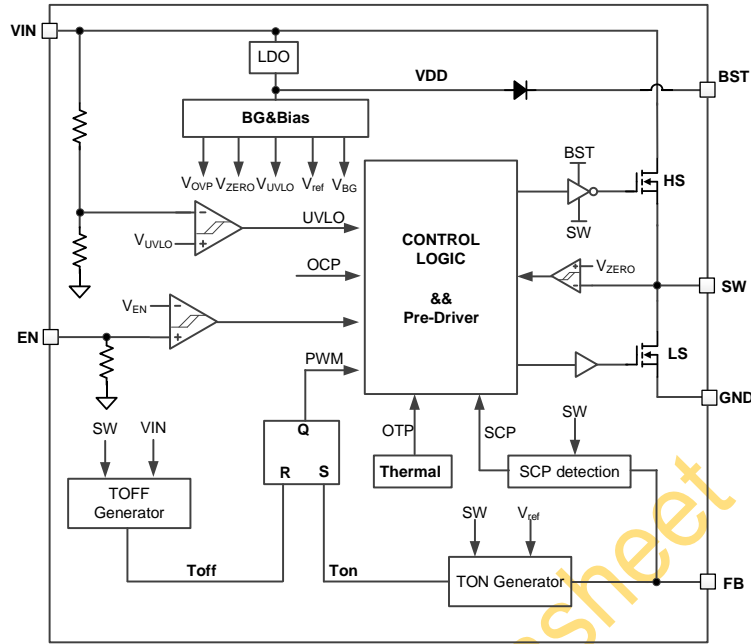


Figure 14. V_{OUT}=1.1V, Efficiency, L=1uH

Preliminary Data



Functional Block Diagram



Preliminary Datasheet



Detailed Description

Overview

The LP6462 is a 2A synchronous buck converter, supporting 4.2-30V input voltage range. The adaptive COT control scheme enables fast transient respond and minimizes the output capacitance. The LP6462 supports both aluminum polymer capacitors and low-ESR ceramic capacitors without external compensation circuit. The LP6462 automatically transfers between PFM and PWM according to the output current.

Under Voltage Lockout (UVLO)

When the input voltage V_{IN} is lower than the UVLO threshold, all functions are shut down. When the input voltage is higher than the UVLO rising threshold, the LP6462 can be enabled by the EN pin.

EN Control

The EN pin can be used to control the system power-up sequence. A precise voltage reference is used as the threshold. When the V_{IN} is above the UVLO threshold and EN voltage rises above the EN pin logic high threshold (1.2V typically), the LP6462 enables all the internal circuits, delays for 260us, and begins the soft-start (refer to Soft-start section for more details).

The EN pin has an internal 1000k Ω pull-down resistor to ground.

Soft-start

The LP6462 integrates soft-start function with a typical time of 600us (t_{ss}). After passing the UVLO threshold and enabled by the EN pin with the 250us delay(t_d), the internal reference voltage ramps from zero to the V_{ref} in 600us and the output voltage ramps up accordingly.

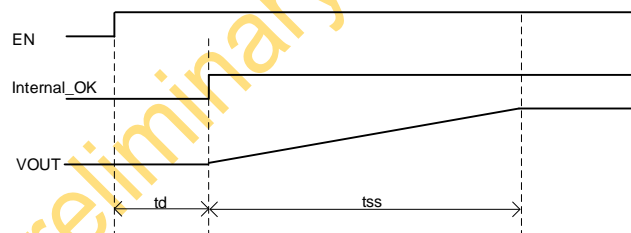


Figure 15. Soft Start Sequence

Constant-ON Time (COT) Control Scheme

The LP6462 integrates the COT control scheme for pseudo-fixed- frequency operation when operating in continuous conduction mode (CCM). Refer to the Functional Block Diagram for better understanding of the operation. The internal on-time (TON) generator block monitors the FB-pin voltage and turns on the high-side MOSFET to start a switching cycle, when the FB-pin voltage drops to an internal reference voltage V_{ref} . Then the internal circuits start to calculate the on-time of the high-side MOSFET, which is proportional to the input voltage and inversely proportional to the output voltage. Once the on-time is finished, the TOFF generator turns off the high-side MOSFET and turns on the low-side MOSFET.

PFM Operation

The LP6462 is designed to maintain high efficiency at light load by adopting pulse-frequency modulation (PFM). In the PFM, the switching cycle is still initiated by the TON generator monitoring the FB-pin voltage. The high-side MOSFET is turned on for TON time and then turned off, followed by turning on the low-side MOSFET. The inductor current falls when the low-side MOSFET is on. When the inductor current reaches zero, detected by the zero-current detection (ZCD) comparator, the low-side MOSFET is turned off, together with the high-side MOSFET. Both MOSFETs remains off until a new switching cycle begins, determined by TON generator. As the load current decreases, the duration for both MOSFETs to remain off increases, leading to a lower switching frequency and higher power efficiency.



FPWM Operation (LP6462F, LP6462HF)

The LP6462F/LP6462HF is designed to work at FPWM to maintain the good load regulation and transient performance. When the output decreases, the inductor is allowed to flow from the output to the ground plane. In this way, the switching frequency is kept the same even without load.

The FPWM operation mode reduced the output ripple under light load at the cost of lower light load efficiency.

Bootstrap Capacitor

The LP6462 integrates two N-MOSFET to achieve high efficiency. The high-side MOSFET is powered by the bootstrap capacitor CBST, which is between the BST pin and SW pin.

Over Current Protection and Short Circuit Protection

The LP6462 protects an over current situation by limiting the inductor valley current. The current of low-side MOSFET is monitored all the time to sense the inductor valley current when the LP6462 is enabled. The high-side MOSFET cannot be turned on if the valley current is higher than the low-side valley current limit, protecting the inductor current from further increasing. The inductor current is limited to the valley current limit plus a half of the inductor ripple current.

The SCP is realized by monitoring the FB-pin voltage when the inductor current is limited. Once the output load draws more current than the current limit, the output voltage drops. When the FB voltage drops to 50% of the V_{ref} for 1-ms, the LP6462 shuts down. The LP6462 will restart after a typical 10-ms hiccup waiting time. If the SCP condition still holds after soft-start, the LP6462 shutdown again, repeating the hiccup operation.

When the over current condition is removed, the output voltage returns to normal operation.

Thermal Protection

The LP6462 has a thermal protection function. The device will shut down when the internal temperature is higher than 160°C and will restart after the temperature drops below 135°C.

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Application Information

Design Requirements

The table 1 shows the design parameters for a typical 5V output voltage in the IPC application.

Table 1 Design Parameters

Parameter	Target
Input voltage range	9~30V
Output voltage	5V
Transient ripple	±200mV
Operating frequency	1000kHz

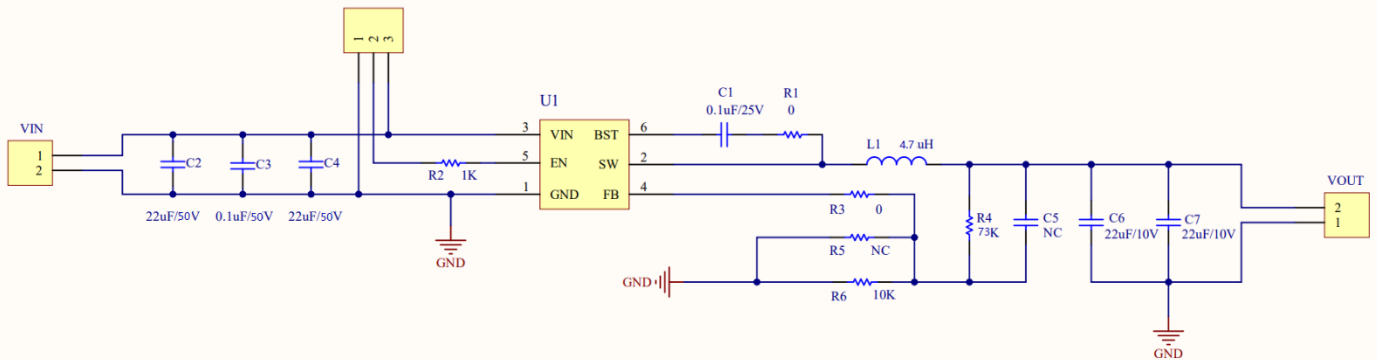


Figure 16. Typical schematic

Output Voltage Setting

The output voltage can be programmed by adjusting the external resistor divider R_{UP} and R_{DOWN} according to the equation below:

$$V_{OUT} = \left(\frac{R_{UP}}{R_{DOWN}} + 1 \right) * V_{ref}$$

When the output voltage is in regulation, the typical voltage at FB pin is 0.6V.

For better accuracy, the R_{DOWN} is recommended to be lower than 100kΩ to ensure the current flowing through R_{DOWN} is at least 100 times larger than the FB pin leakage current.

For a 5V-output application, a 10kΩ R_{DOWN} is selected and the R_{UP} is 73.2kΩ.

A resistor with higher than 1kΩ but lower than 100kΩ should be placed between the resistor divider and FB pin if a C_{ff} capacitor is soldered.

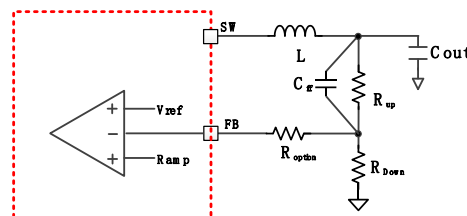


Figure 17. FB connection



EN Design

The LP6462X allows the user to design a precise VIN voltage to enable the converter during power on. The startup sequence can be designed by adjusting the resistor divider of R_{UP_EN} and R_{DOWN_EN} with the equation below,

$$V_{EN} = \frac{1000k\Omega/R_{DOWN_EN}}{R_{UP_EN} + 1000k\Omega/R_{DOWN_EN}} * V_{IN}$$

where V_{EN} is the EN rising threshold voltage at which the converter is enabled, which is 1.2V typically. A 47pF-1nF capacitor is recommend to be soldered in parallel with the R_{EN_DOWN} to avoid the high-frequency noise influence from the switching node.

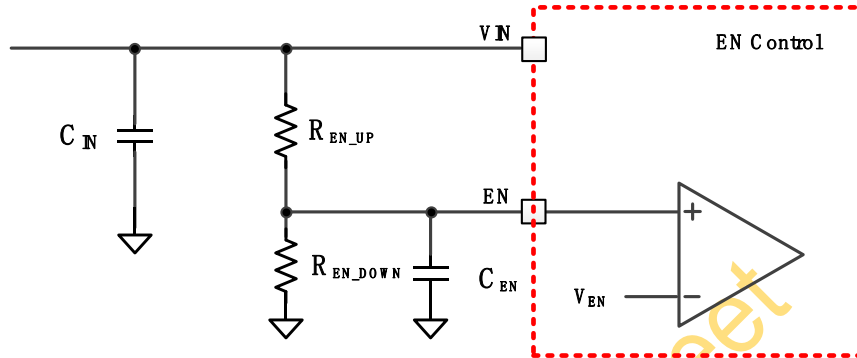


Figure 18. EN connection

Inductor and Output Capacitor Setting

The inductor ripple is calculated by the equation below:

$$I_{PP} = \left(\frac{V_{OUT}}{L * F_{SW}} * \frac{V_{IN} - V_{OUT}}{V_{IN}} \right)$$

To get a better efficiency, the inductor ripple is recommended to be controlled under 40% of the output current to minimize the AC loss of the inductor and power MOSFETs.

For a typical 12V input voltage and 5V output voltage, a low DCR value, 2.2-μH inductor is recommended.

The output capacitor not only impacts the output ripple but also the loop stability. Please follow the design rules in the table below. A feedforward capacitor C_{FF} can be selected to improve the transient behavior. The typical capacitance can be 10-100pF. For this design, 10V, X5R, 22μF capacitors (GRM21BR61A226ME51) from Murata are soldered at the V_{OUT} to GND. Multiple capacitors should be soldered to keep the system stable because of the voltage rating effect.

Table 2 Recommend R/L/C values (LP6462H/F)

Vout	Inductor-L	Cout	R _{UP}	R _{DOWN}	R _{option}	C _{ff}
1.2V	1μH/1.2μH	22μF*1	10 kΩ	10 kΩ	0 Ω	NA
3.3V	1.5μH~3.3μH	22μF*2	45 kΩ	10 kΩ	10 kΩ	10-100pF
5.0V	2.2μH ~6.8μH	22μF*2	73.3 kΩ	10 kΩ	10 kΩ	47-100pF

Table 3 Recommend R/L/C values (LP6462/F)

Vout	Inductor-L	Cout	R _{UP}	R _{DOWN}	R _{option}	C _{ff}
1.2V	1.5μH/2.2μH	22μF*1	10 kΩ	10 kΩ	0 Ω	NA
3.3V	2.2μH~4.7μH	22μF*2	45 kΩ	10 kΩ	10 kΩ	22-100pF
5.0V	4.7μH ~10μH	22μF*2	73.3 kΩ	10 kΩ	10 kΩ	47-100pF

Bootstrap capacitor

A 0.1-μF ceramic capacitor is needed to supply power for the high-side N-MOSFET driver. The capacitor should be at least 10V.



Input capacitor

A typical 22- μF ceramic capacitor is needed to serve as the bulk capacitor at the VIN pin. An additional 0.1 μF is strongly recommended to provide additional high frequency filtering and should be placed to the VIN pin and GND as close as possible.

Application Waveforms (Vin=12V, L=4.7uH, Cout=22uF*2, LP6462H)

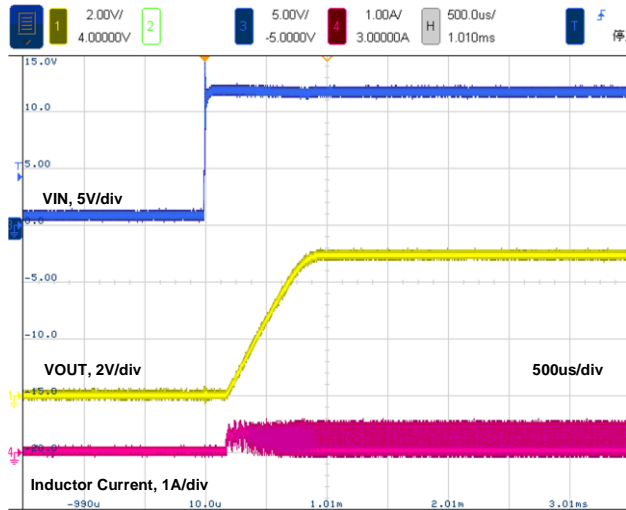


Figure 19. Startup by VIN, 50 Ω load

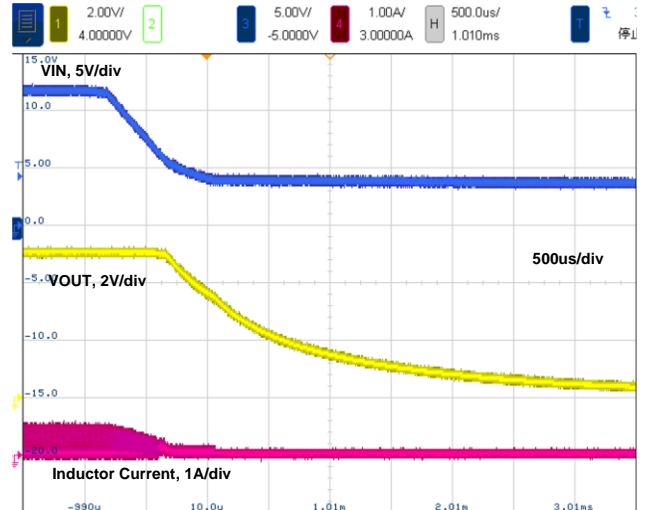


Figure 20. Shutdown by VIN, 50 Ω load

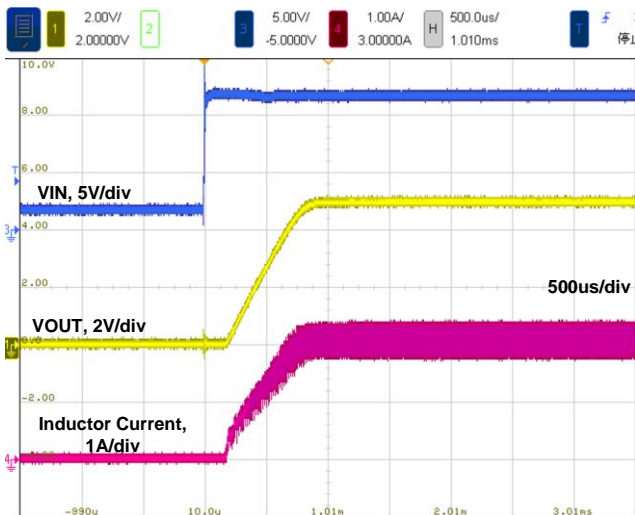


Figure 21. Startup by VIN, 2.5 Ω load

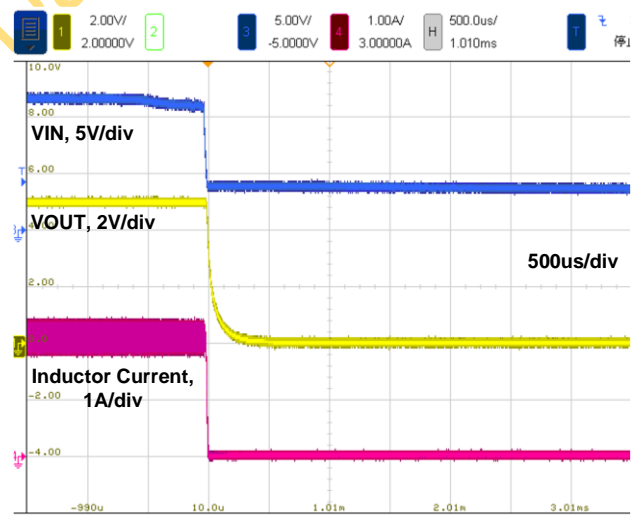


Figure 22. Shutdown by VIN, 2.5 Ω load

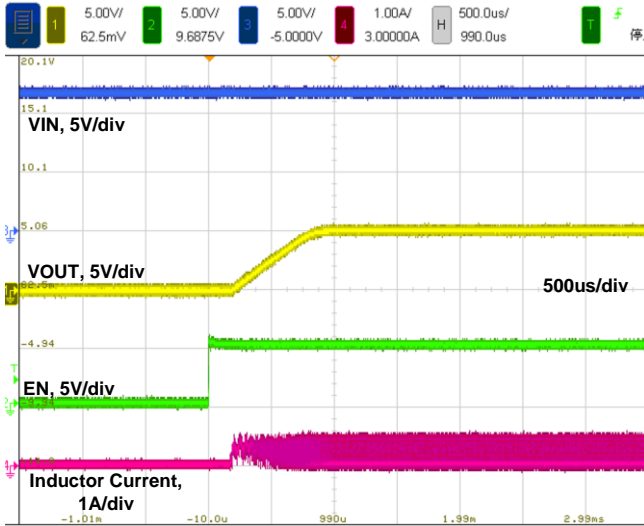


Figure 23. Startup by EN, 50Ω load

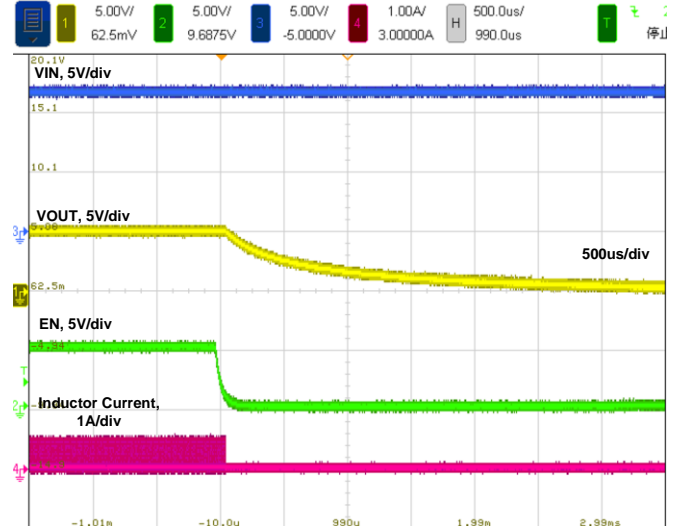


Figure 24. Shutdown by EN, 50Ω load

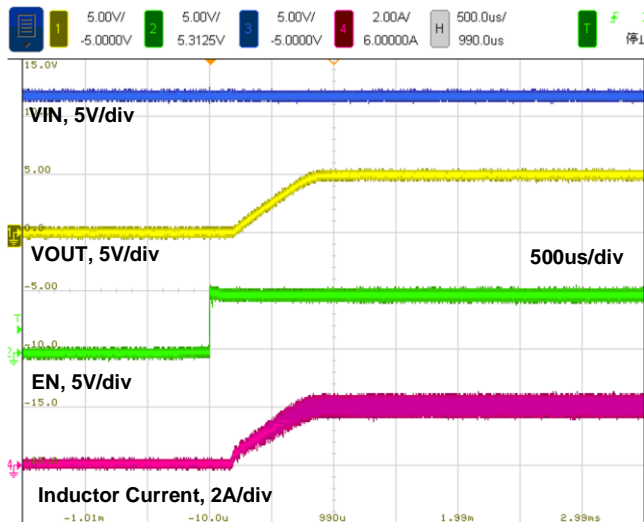


Figure 25. Startup by EN, 2.5Ω load

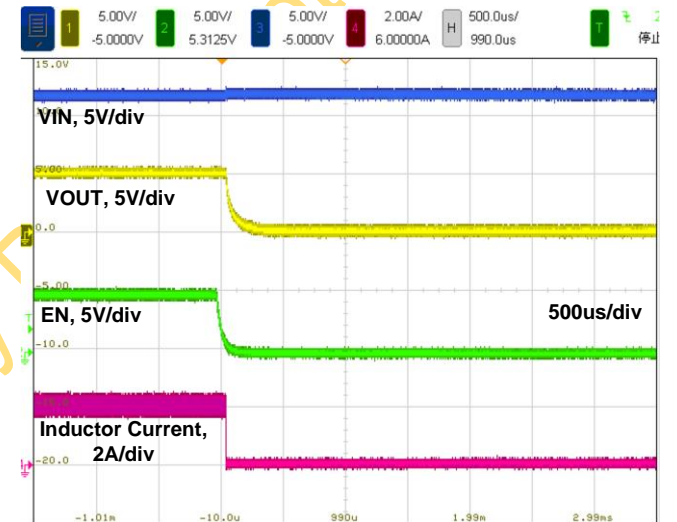


Figure 26. Shutdown by EN, 2.5Ω load

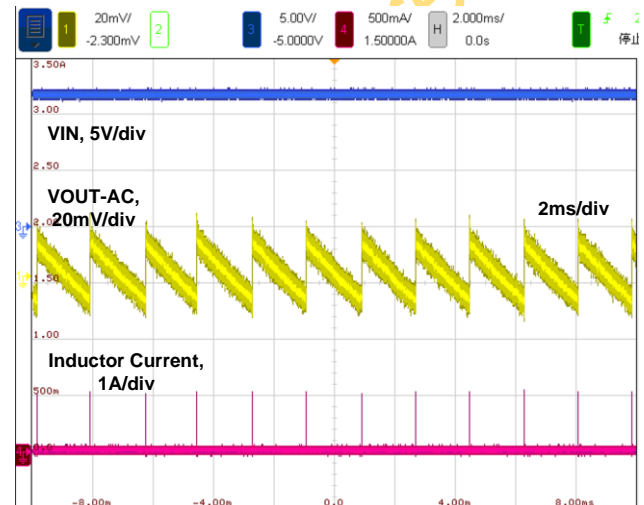


Figure 27. Switching Waveform, 0A load

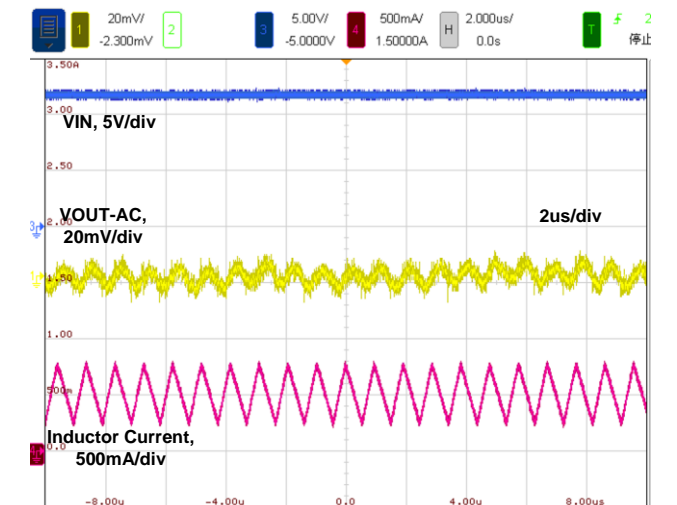


Figure 28. Switching Waveform, 500mA load

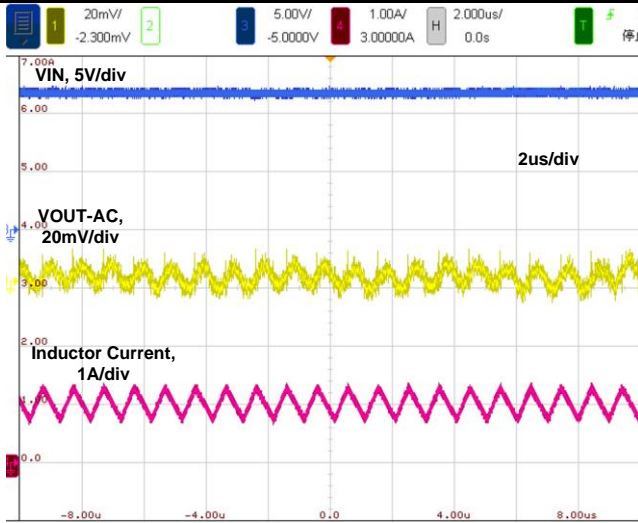


Figure 29. Switching Waveform, 1A load

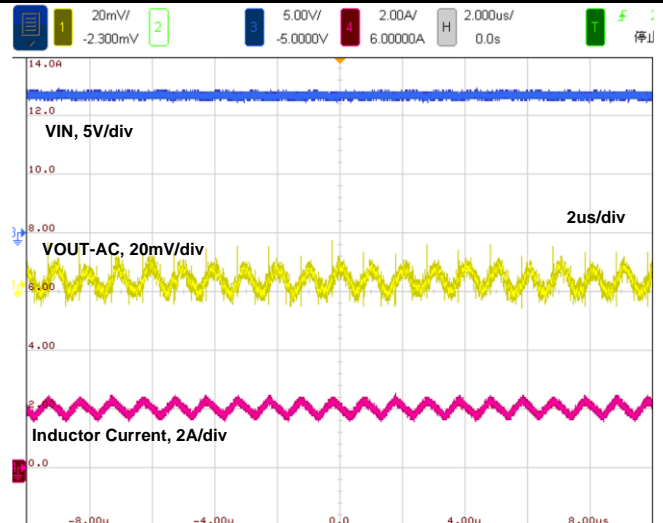


Figure 30. Switching Waveform, 2A load

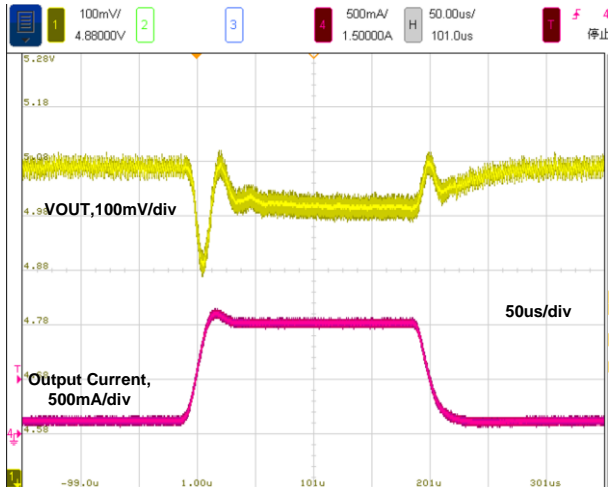


Figure 31. Load Transient, 0.1A-1A-0.1A

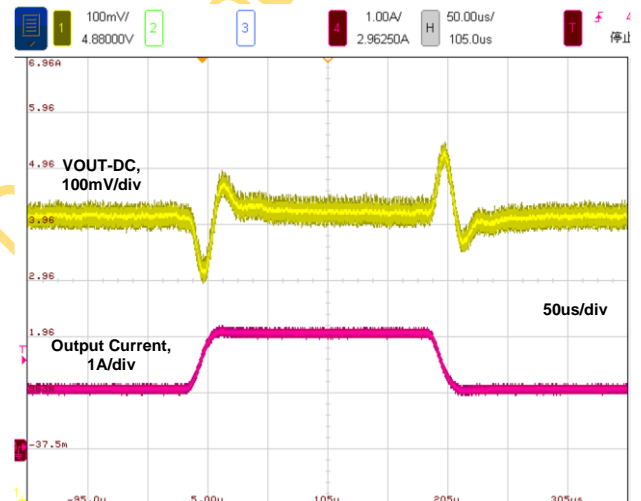


Figure 32. Load Transient, 1A-2A-1A

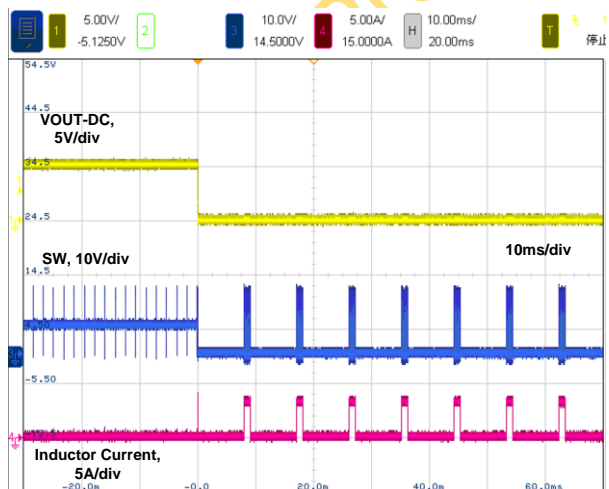


Figure 33. SCP Happen, Hiccup Operation

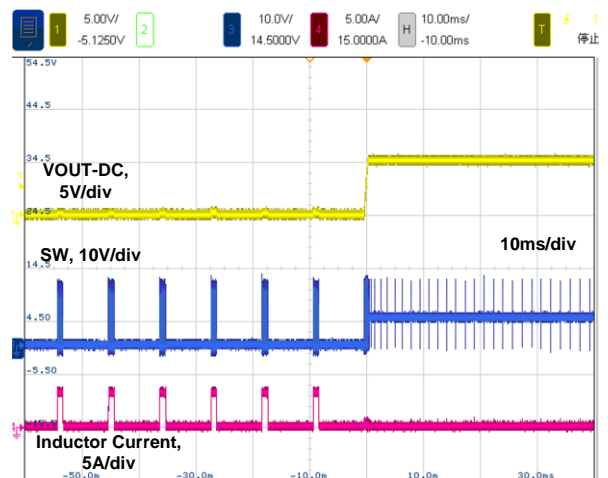


Figure 34. SCP Recovery



PCB Layout Guidelines

Proper layout of the components to minimize high frequency current path loop is important to prevent electrical and magnetic field radiation and high frequency resonant problems. Follow this specific order carefully to achieve the proper layout.

- Place input capacitor (C_2 and C_4) as close as possible to VIN pin and GND pin and use shortest copper trace connection or GND plane.
- Put output capacitor near to the inductor output terminal and the device. Ground connections need to be tied to the IC ground with a short copper trace or GND plane
- Place inductor input terminal to SW pin as close as possible and limit SW node copper area to lower electrical and magnetic field radiation. Do not use multiple layers in parallel for this connection. Minimize parasitic capacitance from this area to any other trace or plane.
- R_1 is reserved to slow down the switching speed for noise sensitive applications and R_3 with higher than $1k\Omega$ resistor should be soldered if the feedforward capacitor is soldered at the same time.

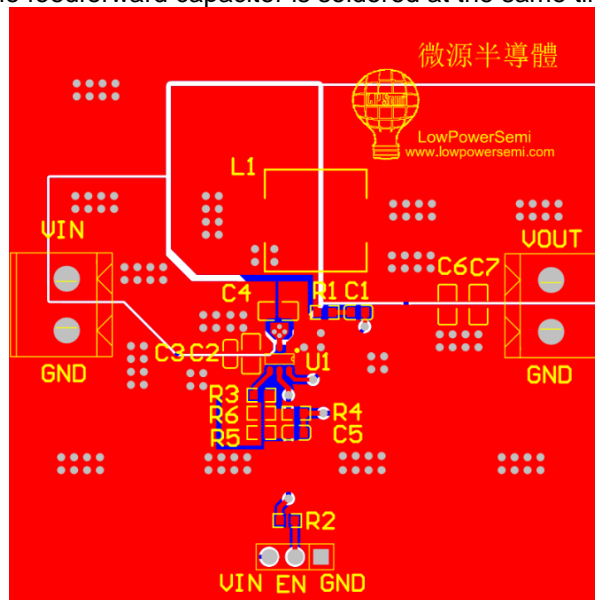
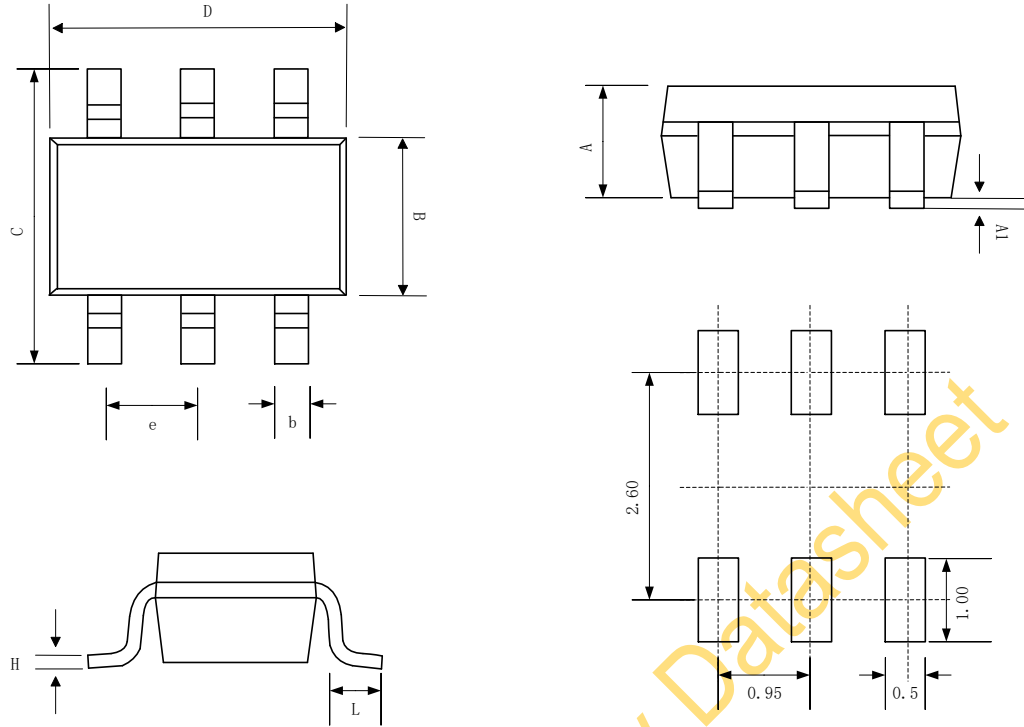


Figure 35 Layout example



Packaging Information

1.6x2.9 SOT23-6 package



Recommended Land Pattern

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.889	1.100	1.295
A1	0.000	0.050	0.152
B	1.397	1.600	1.803
b	0.28	0.35	0.559
C	2.591	2.800	3.000
D	2.692	2.920	3.120
e	0.95BSC		
H	0.080	0.152	0.254
L	0.300	0.450	0.610



Revision History

Revision	Date	Change Description
Rev 1p0	10/5/2022	First release version

Preliminary Datasheet